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orm 1449/PTO Application Number 10/765.671 Filing Date January 26, 2004 INFORMATION DISCLOSURE First Named Inventor Jonathan A. HACK STATEMENT BY APPLICANT Art Unit 2815 (use as many sheets as necessary) **Examiner Name** Jerome JACKSON, Jr. Sheet 1 of 1 **Attorney Docket Number** OTHER DOCUMENTS - NON-PATENT LITERATURE DOCUMENTS Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the TRANSLATION Cžo item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue No. ططلتها number(s), publisher, city and/or country where published NO T. KSUBAKI et al., "Hall resistance hysteresis in AlGaN/GaN 2DEG," Physica E 21 (2004) 676-678. M. BOLDUC et al., "Above room temperature ferromagnetism in Mn-ion implanted Si," Physical Review B 71 033302 (2005) 033302-1-4. **EXAMINER SIGNATURE** DATE CONSIDERED \*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.